V60D100C-M3, V60D100CHM3

Vishay General Semiconductor

RoHS COMPLIANT

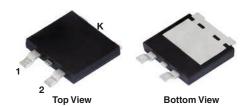
HALOGEN

FREE

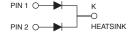
Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.36 \text{ V}$ at $I_F = 5 \text{ A}$

TMBS® eSMP® Series TO-263AC (SMPD)



V60D100C



| PRIMARY CHARACTERISTICS | | | | | |
|-------------------------------------------------------------------|-----------------|--|--|--|--|
| I _{F(AV)} | 2 x 30 A | | | | |
| V _{RRM} | 100 V | | | | |
| I _{FSM} | 320 A | | | | |
| V _F at I _F = 30 A (T _A = 125 °C) | 0.66 V | | | | |
| T _J max. | 150 °C | | | | |
| Package | TO-263AC (SMPD) | | | | |
| Diode variations Dual common cathode | | | | | |

FEATURES

- Trench MOS Schottky technology
- Very low profile typical height of 1.7 mm
- Ideal for automated placement
- · Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified available:
 - Automotive ordering code: base P/NHM3
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

TYPICAL APPLICATIONS

For use in high frequency DC/DC converters, switching power supplies, freewheeling diodes, OR-ing diode, and reverse battery protection in commercial, inductrial, and automotive application.

MECHANICAL DATA

Case: TO-263AC (SMPD)

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Base P/NHM3 - halogen-free, RoHS-compliant, and

AEC-Q101 qualified

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 and HM3 suffix meets JESD 201 class 2 whisker test

Polarity: As marked

| MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted) | | | | | |
|-----------------------------------------------------------------------------------|------------|-----------------------------------|-------------|------|--|
| PARAMETER | | SYMBOL | V60D100C | UNIT | |
| Maximum repetitive peak reverse voltage | | V _{RRM} | 100 | V | |
| Maximum average forward rectified current (fig. 1) | per device | I _{F(AV)} | 60 | А | |
| | per diode | | 30 | | |
| Peak forward surge current 10 ms single half sine-wave superimposed on rated load | | I _{FSM} | 320 | А | |
| Voltage rate of change (rated V _R) | | dV/dt | 10 000 | V/µs | |
| Operating junction and storage temperature range | | T _J , T _{STG} | -40 to +150 | °C | |

V60D100C-M3, V60D100CHM3

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| ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | | |
|-----------------------------------------------------------------------------------|------------------------|-------------------------|-------------------------------|------|------|------|
| PARAMETER | TEST CONDITIONS | | SYMBOL | TYP. | MAX. | UNIT |
| Instantaneous forward voltage per diode | I _F = 5 A | T _A = 25 °C | V _F ⁽¹⁾ | 0.45 | - | V |
| | I _F = 15 A | | | 0.62 | - | |
| | I _F = 30 A | | | 0.75 | 0.81 | |
| | I _F = 5 A | T _A = 125 °C | | 0.36 | - | |
| | I _F = 15 A | | | 0.54 | - | |
| | I _F = 30 A | | | 0.66 | 0.73 | |
| Reverse current at rated V _R per diode | V _R = 70 V | T _A = 25 °C | I _R (2) | 12 | - | μΑ |
| | | T _A = 125 °C | | 11 | - | mA |
| | V _R = 100 V | T _A = 25 °C | | - | 1000 | μΑ |
| | | T _A = 125 °C | | 27 | 85 | mA |

Notes

 $^{(1)}\,$ Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 5 ms

| THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | |
|-------------------------------------------------------------------------|------------|------------------------------------|----------|--------|--|
| PARAMETER | | SYMBOL | V60D100C | UNIT | |
| Typical thermal resistance | per diode | $R_{	heta JC}$ | 1.8 | - °C/W | |
| | per device | $R_{	heta JC}$ | 0.95 | | |
| | per device | R _{0JM} (2) | 3 | | |
| | per device | R _{0JA} ⁽¹⁾⁽²⁾ | 45 | | |

Notes

(1) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$

 $^{(2)}$ Free air, without heatsink; thermal resistance $R_{\theta JA}$ - junction to ambient; thermal resistance $R_{\theta JM}$ - junction to mount

| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|-------------------|--------------------|--------------|---------------|------------------------------------|
| PACKAGE | PREFERRED P/N | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| TO-263AC (SMPD) | V60D100C-M3/I | 0.55 | I | 2000/reel | 13" diameter plastic tape and reel |
| TO-263AC (SMPD) | V60D100CHM3/I (1) | 0.55 | I | 2000/reel | 13" diameter plastic tape and reel |

Note

(1) AEC-Q101 qualified

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RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

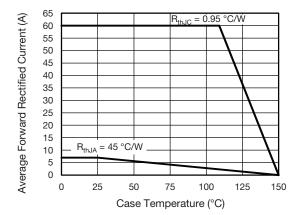
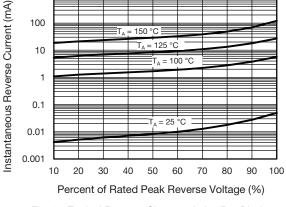


Fig. 1 - Forward Current Derating Curve



1000

Fig. 4 - Typical Reverse Characteristics Per Diode

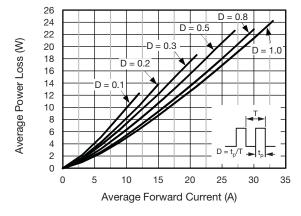


Fig. 2 - Forward Power Loss Characteristics Per Diode

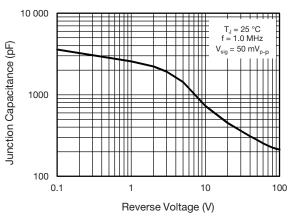


Fig. 5 - Typical Junction Capacitance Per Diode

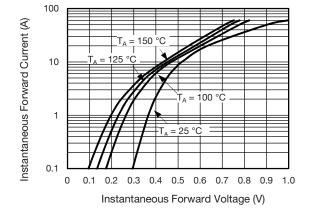


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

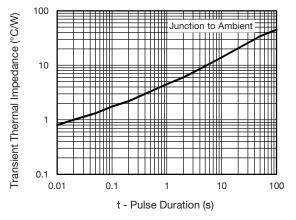


Fig. 6 - Typical Transient Thermal Impedance Per Device

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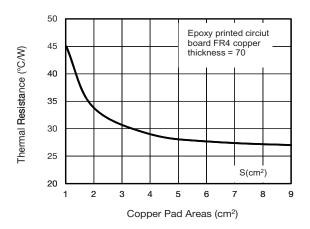
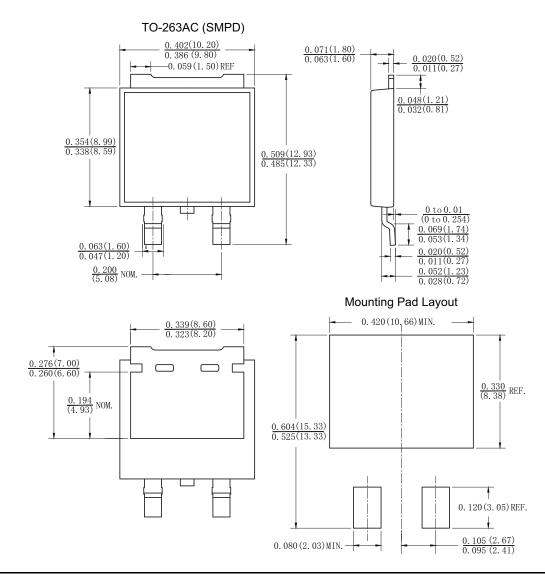


Fig. 7 - Thermal Resistance Junction-to-Ambient vs. Copper Pad Areas

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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